ULAN2001A44CULAN2002A, 24LAN2003A5 ULN2004A DARLINGTON TRANSISTOR ARRAYS

SLRS027 - DECEMBER 1976 - REVISED APRIL 1993

HIGH-VOLTAGE HIGH-CURRENT DARLINGTON TRANSISTOR ARRAYS

- 500-mA Rated Collector Current (Single Output)
- High-Voltage Outputs . . . 50 V
- Output Clamp Diodes
- Inputs Compatible With Various Types of Logic
- Relay Driver Applications
- Designed to Be Interchangeable With Sprague ULN2001A Series

(TOP VIEW) 16 1C 1B 2B [15 2C 14 1 3C 3B [13 **∏** 4C 4B [5B [5 12 1 5C 11 1 6C 6 6B [10 7C 7 7В [Ε 8 9П сом

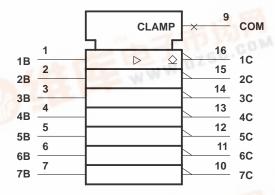
DOR N PACKAGE

description

The ULN2001A, ULN2002A, ULN2003A, and ULN2004A are monolithic high-voltage, high-current Darlington transistor arrays. Each consists of seven npn Darlington pairs that feature high-voltage outputs with common-cathode clamp diodes for switching inductive loads. The collector-current rating of a single Darlington pair is 500 mA. The Darlington pairs may be paralleled for higher current capability. Applications include relay drivers, hammer drivers, lamp drivers, display drivers (LED and gas discharge), line drivers, and logic buffers. For 100-V (otherwise interchangeable) versions, see the SN75465 through SN75469.

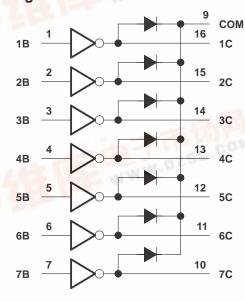
The ULN2001A is a general-purpose array and can be used with TTL and CMOS technologies. The ULN2002A is specifically designed for use with 14- to 25-V PMOS devices. Each input of this device has a zener diode and resistor in series to control the input current to a safe limit. The ULN2003A has a 2.7-k Ω series base resistor for each Darlington pair for operation directly with TTL or 5-V CMOS devices. The ULN2004A has a 10.5-k Ω series base resistor to allow its operation directly from CMOS devices that use supply voltages of 6 to 15 V. The required input current of the ULN2004A is below that of the ULN2003A, and the required voltage is less than that required by the ULN2002A.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram



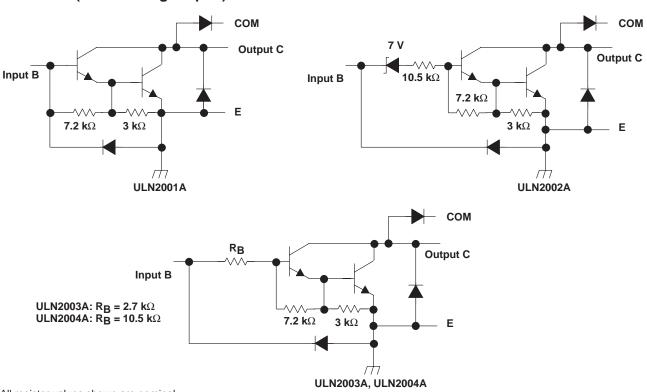




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schematics (each Darlington pair)



All resistor values shown are nominal.

absolute maximum ratings at 25°C free-air temperature (unless otherwise noted)

Collector-emitter voltage	50 V
Input voltage, V _I (see Note 1)	
Peak collector current (see Figures 14 and 15)	500 mA
Output clamp current, I _{OK}	500 mA
Total emitter-terminal current	–2.5 A
Continuous total power dissipation	See Dissipation Rating Table
Operating free-air temperature range, T _A	–20°C to 85°C
Storage temperature range, T _{Stq}	
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

NOTE 1: All voltage values are with respect to the emitter/substrate terminal E, unless otherwise noted.

DISSIPATION RATING TABLE

PACKAGE	T _A = 25°C POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 85°C POWER RATING			
D	950 mW	7.6 mW/°C	494 mW			
N	1150 mW	9.2 mW/°C	598 mW			



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electrical characteristics, $T_A = 25^{\circ}C$ (unless otherwise noted)

PARAMETER TEST		TEST	TEST CONDITIONS		ULN2001A			ULN2002A			UNIT
	PARAMETER	FIGURE	1231 00	TEST CONDITIONS		IN TYP MAX MIN TY		TYP	MAX	UNII	
V _{I(on)}	On-state input voltage	6	V _{CE} = 2 V,	$I_C = 300 \text{ mA}$						13	V
			$I_I = 250 \mu A$,	$I_C = 100 \text{ mA}$		0.9	1.1		0.9	1.1	V
V _{CE(sat)}	Collector-emitter saturation voltage	5	$I_{I} = 350 \mu A$	I _C = 200 mA		1	1.3		1	1.3	
	Saturation voitage		$I_{I} = 500 \mu A$,	I _C = 350 mA		1.2	1.6		1.2	1.6	
٧F	Clamp forward voltage	8	$I_F = 350 \text{ mA}$			1.7	2		1.7	2	V
	Collector cutoff current	1	V _{CE} = 50 V,	I _I = 0			50			50	
ICEX		2	V _{CE} = 50 V, T _A = 70°C	I _I = 0			100			100	μΑ
				V _I = 6 V						500	
I(off)	Off-state input current	3	V _{CE} = 50 V, T _A = 70°C	I _C = 500 μA,	50	65		50	65		μΑ
II	Input current	4	V _I = 17 V						0.82	1.25	mA
1-	01	7	$V_R = 50 V$,	TA = 70°C			100			100	,
^I R	Clamp reverse current		′	V _R = 50 V				50			50
hFE	Static forward current transfer ratio	5	V _{CE} = 2 V,	I _C = 350 mA	1000						
Ci	Input capacitance		V _I = 0,	f = 1 MHz		15	25		15	25	pF

electrical characteristics, $T_A = 25^{\circ}C$ (unless otherwise noted)

	DADAMETED	TEST	TEGT COMPLETIONS		ULN2003A			ULN2004A				
PARAMETER		FIGURE	TEST CONDITIONS		MIN	TYP	MAX	MIN	TYP	MAX	UNIT	
	On-state input voltage	6	V _{CE} = 2 V	I _C = 125 mA						5	٧	
				$I_C = 200 \text{ mA}$			2.4			6		
Viv.				$I_C = 250 \text{ mA}$			2.7					
VI(on)				$I_C = 275 \text{ mA}$						7		
				$I_C = 300 \text{ mA}$			3					
				I _C = 350 mA						8		
	Collector-emitter saturation voltage	5	$I_I = 250 \mu A$,	I _C = 100 mA		0.9	1.1		0.9	1.1	V	
V _{CE(sat)}			$I_I = 350 \mu A$,	I _C = 200 mA		1	1.3		1	1.3		
			$I_I = 500 \mu A$,	$I_C = 350 \text{ mA}$		1.2	1.6		1.2	1.6		
ICEX	Collector cutoff current	1	$V_{CE} = 50 \text{ V},$	I _I = 0			50			50		
		2	V _{CE} = 50 V, T _A = 70°C	I _I = 0			100			100	μΑ	
				V _I = 1 V						500		
٧ _F	Clamp forward voltage	8	$I_F = 350 \text{ mA}$			1.7	2		1.7	2	V	
I _{I(off)}	Off-state input current	3	V _{CE} = 50 V, T _A = 70°C	$I_C = 500 \mu A$,	50	65		50	65		μΑ	
	Input current	4	V _I = 3.85 V			0.93	1.35					
lı			V _I = 5 V						0.35	0.5	mA	
			V _I = 12 V						1	1.45		
IR	Clamp reverse current	7	V _R = 50 V				50			50	T	
			$V_R = 50 V$,	T _A = 70°C			100			100	μΑ	
Ci	Input capacitance		$V_{I} = 0,$	f = 1 MHz		15	25		15	25	pF	



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switching characteristics, $T_A = 25^{\circ}C$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
tPLH	Propagation delay time, low-to-high-level output	See Figure 9		0.25	1	μs
tPHL	Propagation delay time, high-to-low-level output	See Figure 9		0.25	1	μs
VOH	High-level output voltage after switching	$V_S = 50 \text{ V},$ $I_O \approx 300 \text{ mA},$ See Figure 10	V _S -20			mV

PARAMETER MEASUREMENT INFORMATION

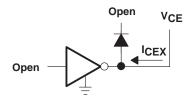


Figure 1. I_{CEX} Test Circuit

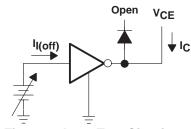
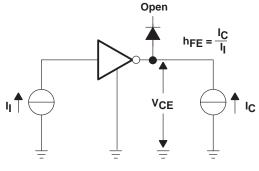


Figure 3. I_{I(off)} Test Circuit



NOTE: I_I is fixed for measuring $V_{\text{CE(sat)}}$, variable for measuring h_{FE} .

Figure 5. h_{FE}, V_{CE(sat)} Test Circuit

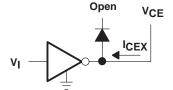


Figure 2. I_{CEX} Test Circuit

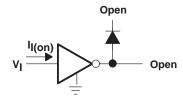


Figure 4. I_I Test Circuit

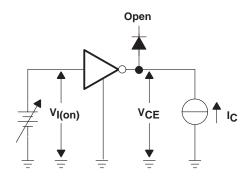


Figure 6. V_{I(on)} Test Circuit

PARAMETER MEASUREMENT INFORMATION



Figure 7. I_R Test Circuit

Figure 8. V_F Test Circuit

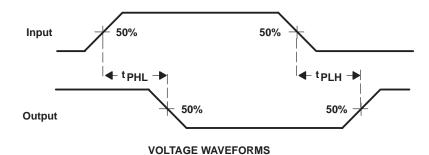
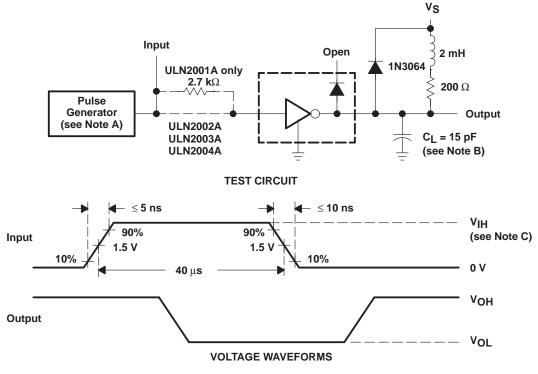


Figure 9. Propagation Delay Time Waveforms

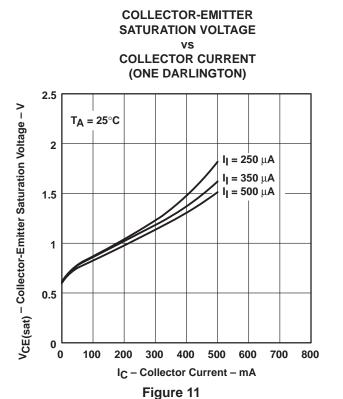


- NOTES: A. The pulse generator has the following characteristics: PRR = 12.5 kHz, Z_O = 50 Ω .
 - B. C_I includes probe and jig capacitance.
 - C. For testing the ULN2001A and the ULN2003A, V_{IH} = 3 V; for the ULN2002A, V_{IH} = 13 V; for the ULN2004A, V_{IH} = 8 V.

Figure 10. Latch-Up Test Circuit and Voltage Waveforms



TYPICAL CHARACTERISTICS



COLLECTOR-EMITTER
SATURATION VOLTAGE
vs
TOTAL COLLECTOR CURRENT
(TWO DARLINGTONS PARALLELED)

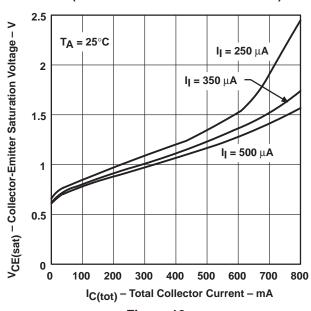


Figure 12

COLLECTOR CURRENT

INPUT CURRENT 500 $R_L = 10 \Omega$ 450 T_A = 25°C I_C - Collector Current - mA 400 V_S = 10 V 350 V_S = 8 V 300 250 200 150 100 50 0 0 25 100 125 150 175 200 I_I - Input Current - μA

Figure 13



THERMAL INFORMATION

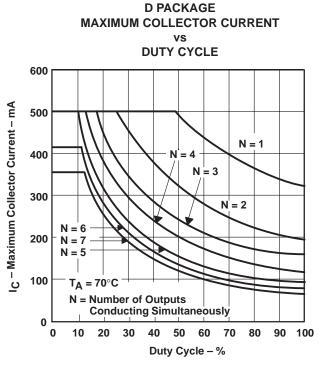


Figure 14

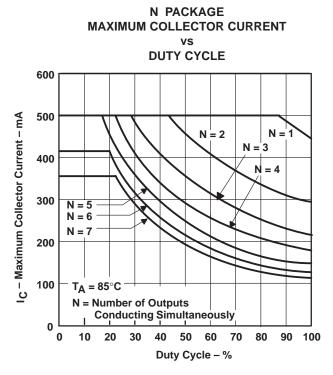


Figure 15



APPLICATION INFORMATION

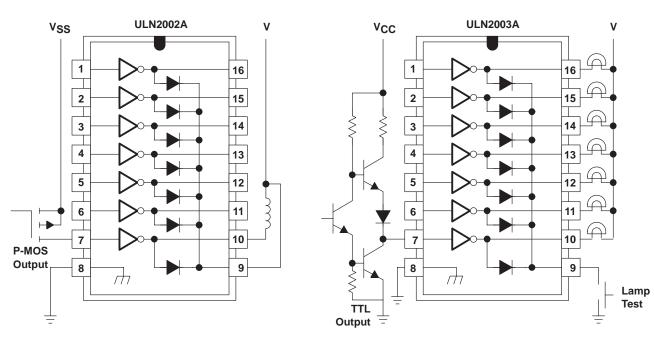


Figure 16. P-MOS to Load

Figure 17. TTL to Load

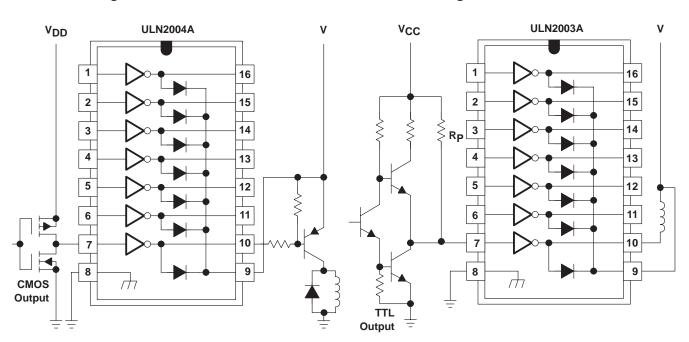


Figure 18. Buffer for Higher Current Loads

Figure 19. Use of Pullup Resistors to Increase Drive Current



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